



Package: 9 pin, 11.0 mm x 8.5 mm x 1.375mm

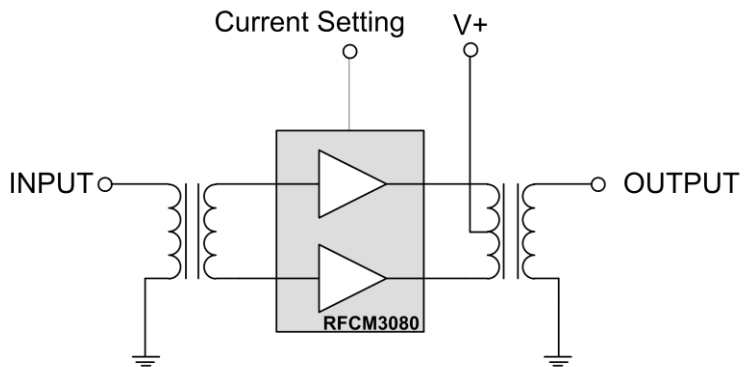


**Features**

- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under all Terminations
- 27.5dB Min. Gain at 1003MHz
- 270mA Max. at 24VDC

**Applications**

- 40MHz to 1003MHz CATV Amplifier Systems



Functional Block Diagram

**Product Description**

The RFCM3080 is a Push Pull amplifier SMD module. The part employs GaAs MESFET, GaAs pHEMT and GaN HEMT die and is operated from 40MHz to 1003MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability. DC current of the device can be externally adjusted for optimum distortion performance vs. power consumption over a wide range of output level.

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**Ordering Information**

RFCM3080SB	Sample Bag 5 pieces
RFCM3080SQ	Sample Bag 25 pieces
RFCM3080SR	7" Reel with 100 pieces
RFCM3080TR7	7" Reel with 500 pieces
RFCM3080TR13	13" Reel with 1000 pieces
RFCM3080PCBA-410	Fully Assembled Evaluation Board
RFCM3080PCK-410	Fully Assembled Evaluation Board with Sample Pack

**Optimum Technology Matching® Applied**

<input type="checkbox"/> GaAs HBT	<input type="checkbox"/> SiGe BiCMOS	<input checked="" type="checkbox"/> GaAs pHEMT	<input checked="" type="checkbox"/> GaN HEMT
<input checked="" type="checkbox"/> GaAs MESFET	<input type="checkbox"/> Si BiCMOS	<input type="checkbox"/> Si CMOS	<input type="checkbox"/> RF MEMS
<input type="checkbox"/> InGaP HBT	<input type="checkbox"/> SiGe HBT	<input type="checkbox"/> Si BJT	<input type="checkbox"/> LDMOS

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**Absolute Maximum Ratings**

Parameter	Rating	Unit
RF Input Voltage (single tone)	70	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					V+= 24V; TMB=30°C; ZS=ZL=75Ω
Power Gain		27.0		dB	f=50MHz
	27.5	28.5	29.0	dB	f=1003MHz
Slope <sup>[1]</sup>	0.5	1.0		dB	f=40MHz to 1003MHz
Flatness of Frequency Response			0.8	dB	f=40MHz to 1003MHz
Input Return Loss	-20			dB	f=40MHz to 320MHz
	-18			dB	f=320MHz to 640MHz
	-17			dB	f=640MHz to 870MHz
	-16			dB	f=870MHz to 1003MHz
Output Return Loss	-20			dB	f=40MHz to 320MHz
	-19			dB	f=320MHz to 640MHz
	-18			dB	f=640MHz to 870MHz
	-17			dB	f=870MHz to 1003MHz
Noise Figure		4.5	5.0	dB	f=50MHz to 1003MHz
Total Current Consumption (DC)		250.0	270.0	mA	
<b>Distortion data 40MHz to 550MHz</b>					V+= 24V; TMB=30°C; ZS=ZL=75Ω
CTB		-70	-65	dBc	V <sub>0</sub> =46dBmV flat, 79 analog channels plus 75 digital channels (-6dB offset) <sup>[2]</sup>
XMOD		-63	-58	dBc	V <sub>0</sub> =46dBmV flat, 79 analog channels plus 75 digital channels (-6dB offset) <sup>[2]</sup>
CSO		-75	-66	dBc	V <sub>0</sub> =46dBmV flat, 79 analog channels plus 75 digital channels (-6dB offset) <sup>[2]</sup>
CIN	65	69		dB	V <sub>0</sub> =46dBmV flat, 79 analog channels plus 75 digital channels (-6dB offset) <sup>[2]</sup>

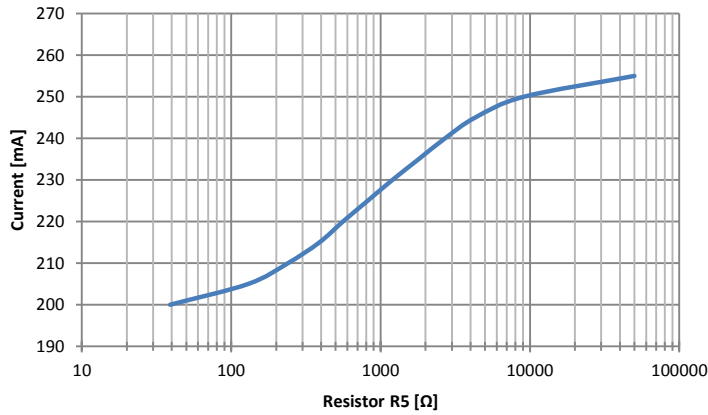
1. The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.
2. 79 analog channels, NTSC frequency raster: 55.25MHz to 547.25MHz, +46dBmV flat output level, plus 75 digital channels, -6dB offset relative to the equivalent analog carrier. Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA. Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA. Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested. Carrier to Intermodulation Noise (CIN) - The CIN parameter is defined by ANSI/SCTE 17 (Test procedure for carrier to noise).

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### Current Adjustment Using Resistor R5

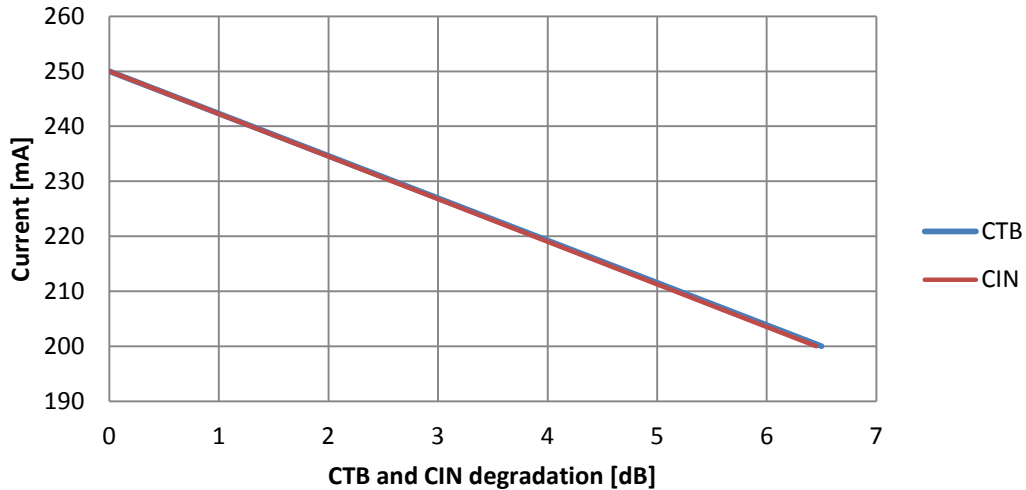
The RFCM3080 can be operated over a wide range of current to provide maximum required performance with minimum current consumption. Changing the value of resistor R5 on application circuit allows a variation of the current between 200mA and 255mA (typ.). Within the range of current between 200mA and 255mA gain (S21) change is less than 0.4dB and noise figure change is less than 0.1dB.

Current vs. Resistor R5



Device Current [mA], typical	R5 [Ω]
255	open
250	9100
245	4300
240	2700
235	1800
230	1200
225	820
220	560
215	390
210	240
205	130
200	39
V+= 24V; T <sub>MB</sub> =30°C; Z <sub>S</sub> =Z <sub>L</sub> =75Ω	

### Distortion Degradation over Device Current, typical values



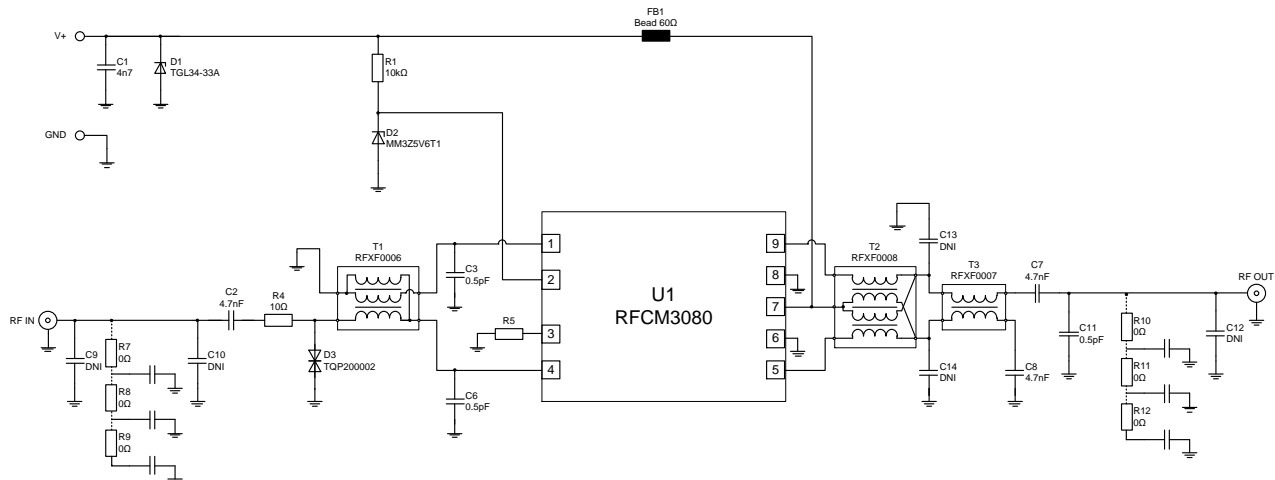
**Test condition:**

V+= 24V; T<sub>MB</sub>=30°C; Z<sub>S</sub>=Z<sub>L</sub>=75Ω;

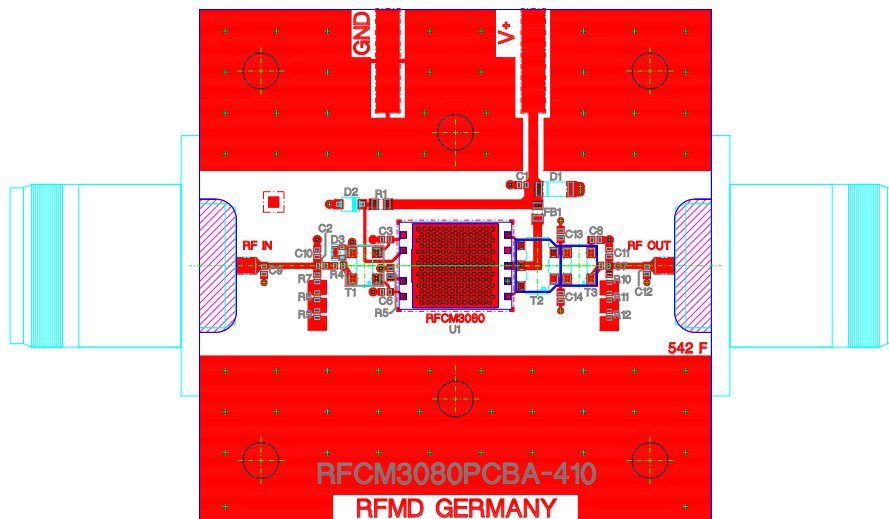
V<sub>0</sub>=46dBmV flat, 79 analog channels plus 75 digital channels (-6dB offset)

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### Application Circuit



### Evaluation Board Layout



**Note:**

The ground plane of the RFCM3080 module should be soldered onto a board equipped with as many thermal vias as possible. Underneath this thermal via array a heat sink with thermal grease needs to be placed which is able to dissipate the complete module DC power (up to 6.5 Watts). In any case the module backside temperature should not exceed 100°C.

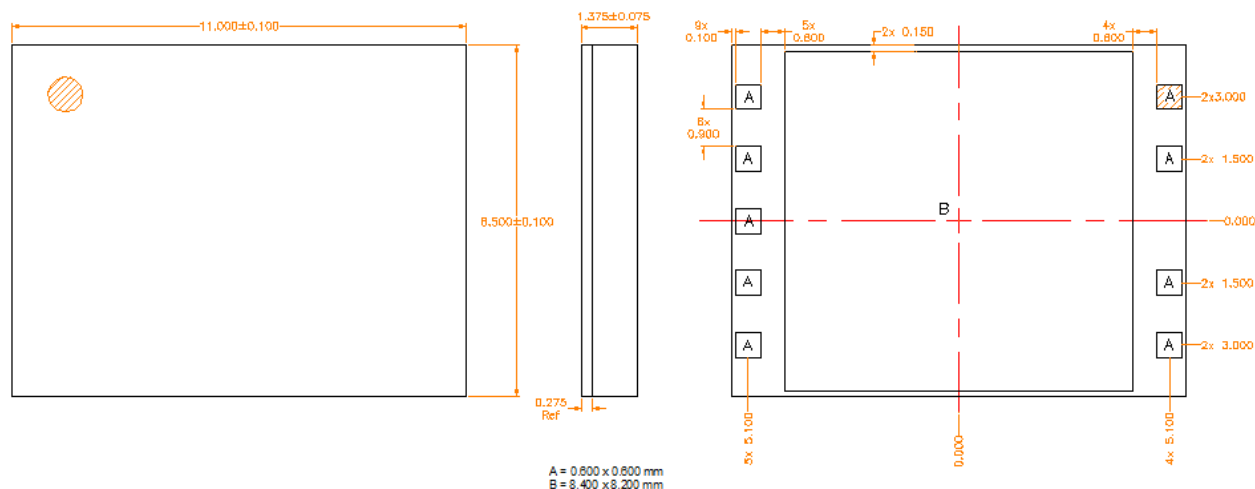
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### Component Chart

Component Type	Value	Qty	Designator	Comment
Capacitor	4.7nF	4	C1, C2, C7, C8	
Capacitor	DNI	5	C9, C10, C12, C13, C14	optional to improve matching in application
Capacitor	0.5pF	3	C3, C6, C11	
Resistor	10kΩ	1	R1	
Resistor	10Ω	1	R4	
Resistor	DNI	6	R7, R8, R9, R10, R11, R12	optional to improve matching in application
Resistor	see page 3	1	R5	optional to set current-value
Impedance Bead	60Ω @ 100MHz	1	FB1	
Transient Voltage Suppressor Diode	TGL34-33A	1	D1	
Zener Diode	MM3Z5V6T1G	1	D2	
ESD Protection Diode	TQP200002	1	D3	
Transformer	RFXF0006	1	T1	
Transformer	RFXF0008	1	T2	
Transformer	RFXF0007	1	T3	
DUT	RFCM3080	1	U1	

### Package Drawing

Dimensions in millimeters



**Pin Configuration**

Pin	Function	Description
1	RF IN (+)	RF AMP Positive Input
2	5.6V V+	Supply Voltage 5.6V
3	IDC Adjust	Current Adjustment
4	RF IN (-)	RF AMP Negative Input
5	RF OUT (-)	RF AMP Negative Output
6	GND	Ground
7	24V V+	Supply Voltage 24V
8	GND	Ground
9	RF OUT (+)	RF AMP Positive Output

